

Silicon NPN Power Transistors

2SC3322

DESCRIPTION

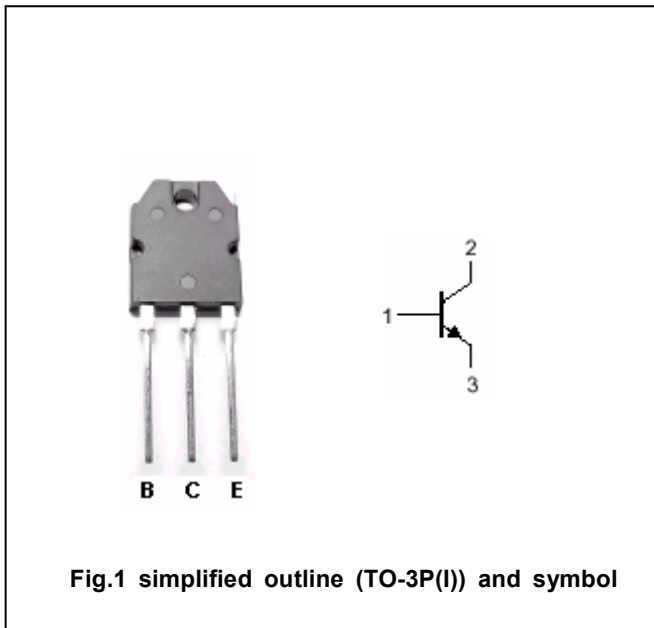
- With TO-3P(I) package
- High voltage
- High speed

APPLICATIONS

- High power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	900	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		10	A
I _B	Base current		2.5	A
P _T	Total power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A, L=100mH; R _{BE} =∞	800			V
V _{(BR)EBO}	Base-emitter breakdown voltage	I _E =10mA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.3A			1.0	V
V _{BE sat}	Base-emitter saturation voltage	I _C =1.5A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			100	μA
I _{CEO}	Collector cut-off current	V _{CE} =650V; R _{BE} =∞			100	μA
h _{FE-1}	DC current gain	I _C =0.5A; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =3A; V _{CE} =5V	7			

Switching times

t _{on}	Turn-on time	I _C =3A; V _{CC} ≈250V I _{B1} =0.6A; I _{B2} =-1.5A			1.0	μs
t _{stg}	Storage time				3.0	μs
t _f	Fall time				1.0	μs

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PACKAGE OUTLINE

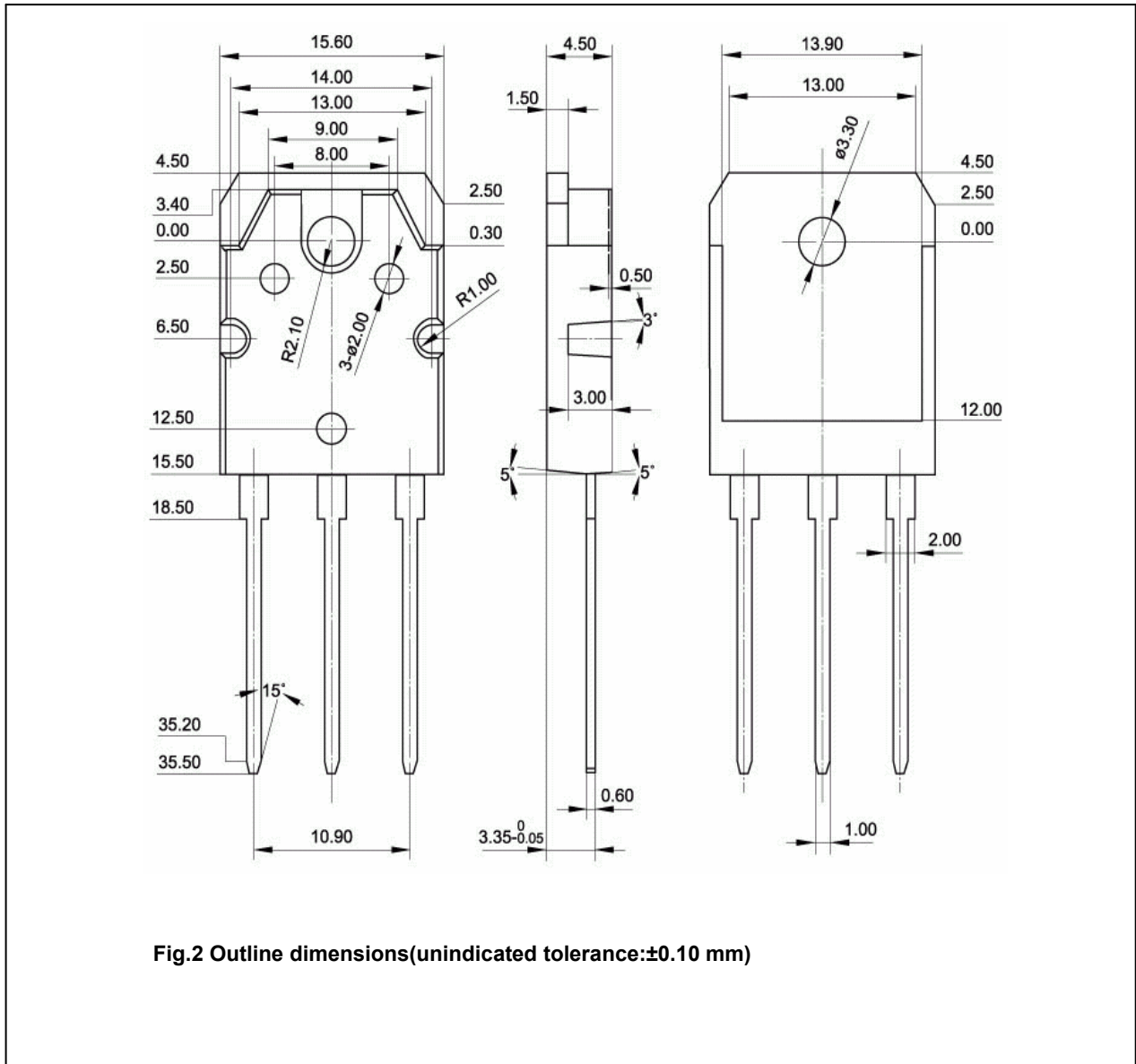


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)